MOSFETs Silicon N-Channel MOS (U-MOSVII)

# **TPCA8087**

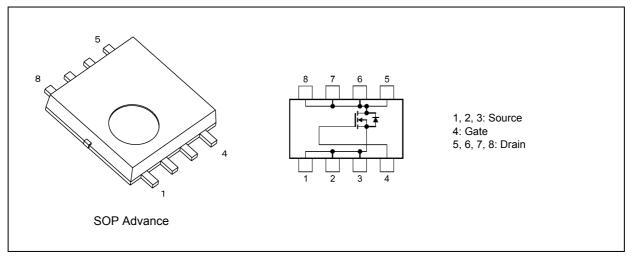
#### 1. Applications

- Notebook PCs
- Mobile Handsets

#### 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 1.5 \text{ m}\Omega$  (typ.) (V<sub>GS</sub> = 10 V)
- (3) Low leakage current:  $I_{DSS}$  = 10  $\mu A$  (max) (V\_{DS} = 30 V)
- (4) Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V (V\_{DS} = 10 V,  $I_{D}$  = 1.0 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteris                   | Symbol                  | Rating   | Unit             |            |    |
|-------------------------------|-------------------------|----------|------------------|------------|----|
| Drain-source voltage          |                         |          | V <sub>DSS</sub> | 30         | V  |
| Gate-source voltage           |                         |          | V <sub>GSS</sub> | ±20        |    |
| Drain current (DC)            |                         | (Note 1) | Ι <sub>D</sub>   | 56         | A  |
| Drain current (pulsed)        |                         | (Note 1) | I <sub>DP</sub>  | 168        |    |
| Power dissipation             | (T <sub>c</sub> = 25°C) |          | PD               | 70         | W  |
| Power dissipation             | (t = 10 s)              | (Note 2) | PD               | 2.8        | W  |
| Power dissipation             | (t = 10 s)              | (Note 3) | PD               | 1.6        | W  |
| Single-pulse avalanche energy |                         | (Note 4) | E <sub>AS</sub>  | 407        | mJ |
| Avalanche current             |                         |          | I <sub>AR</sub>  | 56         | A  |
| Channel temperature           |                         |          | T <sub>ch</sub>  | 150        | °C |
| Storage temperature           |                         |          | T <sub>stg</sub> | -55 to 150 | 7  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

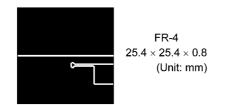
| Characteristics                       |                         |          |                       | Max  | Unit |
|---------------------------------------|-------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | (T <sub>c</sub> = 25°C) |          | R <sub>th(ch-c)</sub> | 1.78 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)              | (Note 2) | R <sub>th(ch-a)</sub> | 44.6 |      |
| Channel-to-ambient thermal resistance | (t = 10 s)              | (Note 3) | R <sub>th(ch-a)</sub> | 78.1 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V\_DD = 24 V, T\_ch = 25°C (initial), L = 0.1 mH, R\_G = 1  $\Omega$ , I\_AR = 56 A



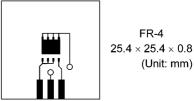
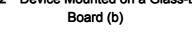


Fig. 5.2 Device Mounted on a Glass-Epoxy

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



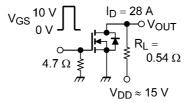
#### 6. Electrical Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

#### 6.1. Static Characteristics

| Characteristics                | Symbol               | Test Condition                                  | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V                | _   | _    | ±0.1 | μA   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V   | —   | _    | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 30  | _    | _    | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V | 15  | _    | _    |      |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA | 1.3 | _    | 2.3  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 28 A  |     | 1.9  | 2.3  | mΩ   |
|                                |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 28 A   |     | 1.5  | 1.9  |      |

#### 6.2. Dynamic Characteristics

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 6400 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 360  | —   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 1200 | _   |      |
| Switching time (rise time)     | t <sub>r</sub>   | See Figure 6.2.1.  | _   | 5.7  | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  |     | 16   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  |     | 11   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 73   | _   |      |



Duty  $\leq$  1%,  $t_W =$  10  $\mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics

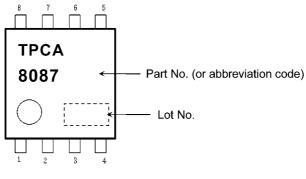
| Characteristics                                    | Symbol           | Test Condition                                       | Min | Тур. | Max | Unit |
|--|------------------|--|-----|------|-----|------|
| Total gate charge<br>(gate-source plus gate-drain) | Qg               | $V_{DD} \approx 24$ V, $V_{GS}$ = 10 V, $I_D$ = 56 A |     | 91   | —   | nC   |
| Gate-source charge 1                               | Q <sub>gs1</sub> |  | _   | 20   | _   |      |
| Gate-drain charge                                  | Q <sub>gd</sub>  |  | _   | 12   | _   |      |

#### 6.4. Source-Drain Characteristics

| Characteristics                 |         | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---------------------------------|---------|------------------|---|-----|------|------|------|
| Pulsed reverse drain current (I | Note 5) | I <sub>DRP</sub> | —   |     | _    | 168  | Α    |
| Diode forward voltage           |         | V <sub>DSF</sub> | I <sub>DR</sub> = 56 A, V <sub>GS</sub> = 0 V |     | _    | -1.2 | V    |

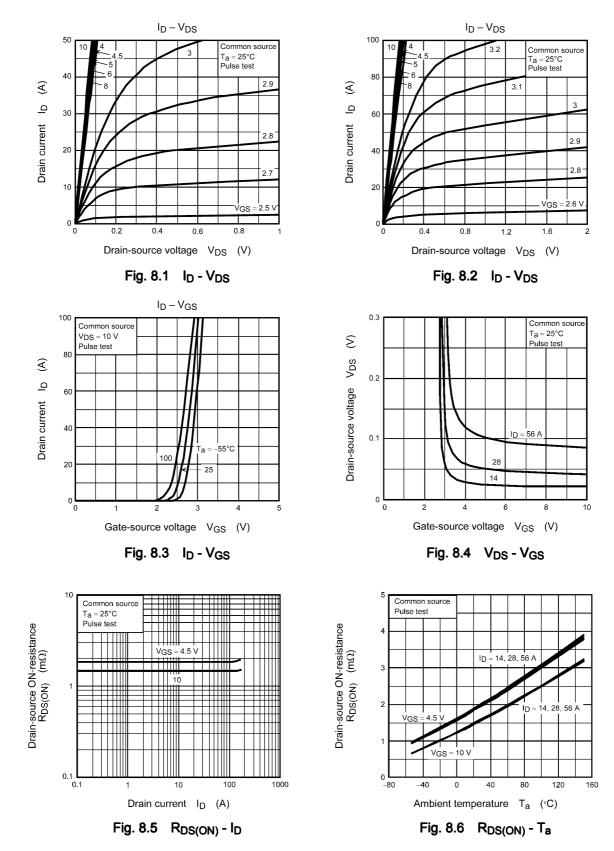
Note 5: Ensure that the channel temperature does not exceed 150°C.

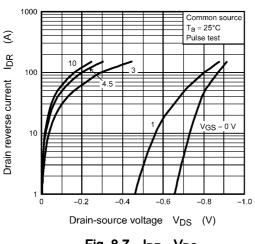
7. Marking



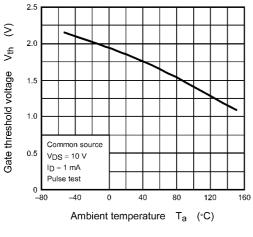


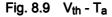
### 8. Characteristics Curves (Note)

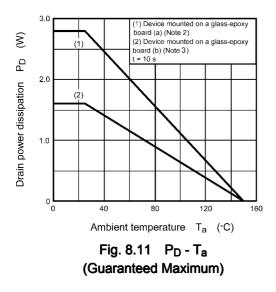


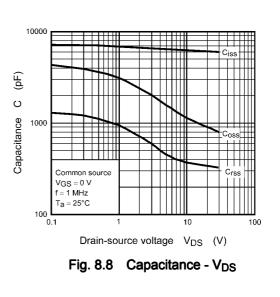












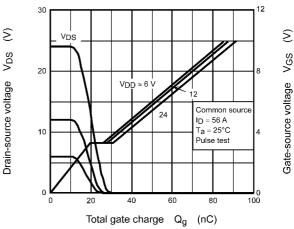
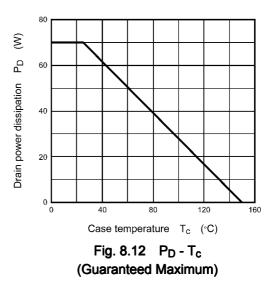
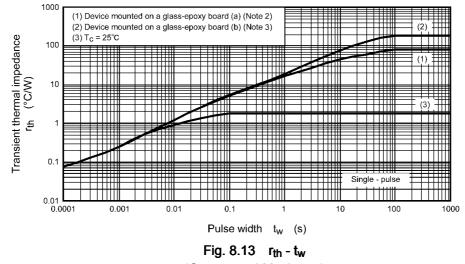


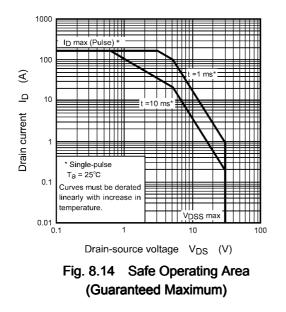
Fig. 8.10 Dynamic Input/Output Characteristics











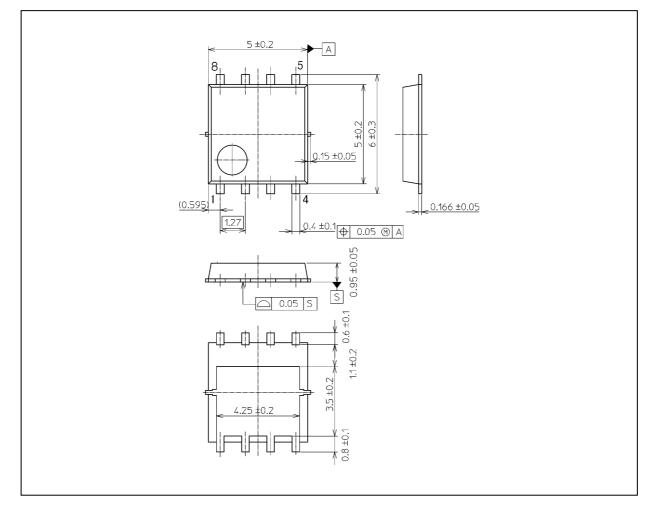
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TPCA8087

#### Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

Package Name(s)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

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